DAP222M3T5G

Preferred Device

Product Preview

Common Anode Silicon Dual Switching Diodes

These Common Anode Silicon Epitaxial Planar Dual Diodes are designed for use in ultra high speed switching applications. The DAP222 device is housed in the SOT–723 package which is designed for low power surface mount applications, where board space is at a premium.

- Fast t_{rr}
- Low C_D
- ESD Performance: Human Body Model; > 2000 V, Machine Model > 200 V
- Available in 4 mm Tape and Reel
- This is a Pb-Free Device

MAXIMUM RATINGS $(T_A = 25^{\circ}C)$

Rating	Symbol	Value	Unit
Reverse Voltage	V_{R}	80	V
Peak Reverse Voltage	V_{RM}	80	V
Forward Current	I _F	100	mA
Peak Forward Current	I _{FM}	300	mA
Peak Forward Surge Current	I _{FSM} (Note 1)	2.0	Α

THERMAL CHARACTERISTICS

Rating	Symbol	Max	Unit
Power Dissipation	P_{D}	260	mW
Junction Temperature	T_J	150	°C
Storage Temperature	T _{stg}	-55 ~ + 150	°C

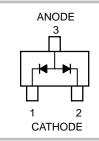
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. $t = 1.0 \mu S$.



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MARKING DIAGRAM



SOT-723 CASE 631AA STYLE 4



P9

= Specific Device Code

M = Date Code

ORDERING INFORMATION

Device	Package	Shipping [†]
DAP222M3T5G	SOT-723	8000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

DAP222M3T5G

ELECTRICAL CHARACTERISTICS $(T_A = 25^{\circ}C)$

Characteristic	Symbol	Condition	Min	Max	Unit
Reverse Voltage Leakage Current	I _R	V _R = 70 V	-	0.1	μΑ
Forward Voltage	V _F	I _F = 100 mA	-	1.2	V
Reverse Breakdown Voltage	V_{R}	I _R = 100 μA	80	_	V
Diode Capacitance	C _D	V _R = 6.0 V, f = 1.0 MHz	-	3.5	pF
Reverse Recovery Time	t _{rr} (Note 2)	I_F = 5.0 mA, V_R = 6.0 V, R_L = 100 Ω , I_{rr} = 0.1 I_R	-	4.0	ns

^{2.} t_{rr} Test Circuit for DAP222 in Figure 4.

DAP222M3T5G

TYPICAL ELECTRICAL CHARACTERISTICS

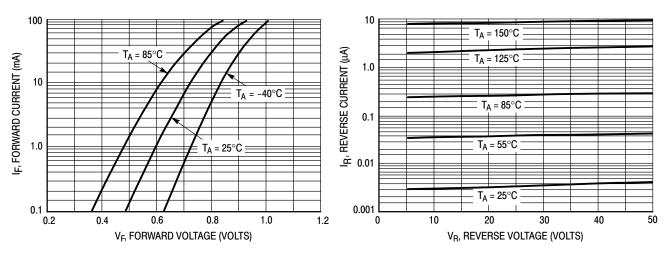


Figure 1. Forward Voltage

Figure 2. Reverse Current

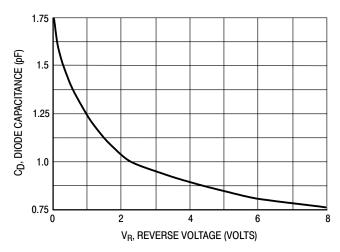


Figure 3. Diode Capacitance

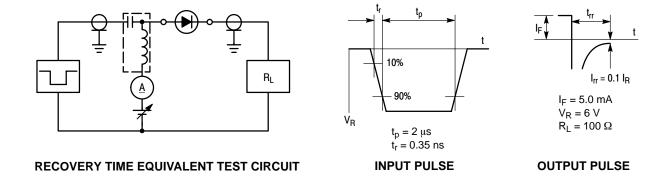


Figure 4. Reverse Recovery Time Test Circuit



SOT-723 CASE 631AA-01 ISSUE D

DATE 10 AUG 2009

NOTES:

- NOTES.

 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

 2. CONTROLLING DIMENSION: MILLIMETERS.

 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD
- FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

	MILLIMETERS		
DIM	MIN	NOM	MAX
Α	0.45	0.50	0.55
b	0.15	0.21	0.27
b1	0.25	0.31	0.37
С	0.07	0.12	0.17
D	1.15	1.20	1.25
E	0.75	0.80	0.85
е	0.40 BSC		
ΗE	1.15	1.20	1.25
L	0.29 REF		
12	0.15	0.20	0.25

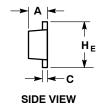
L2 0.15 0.20 0.25 **GENERIC** MARKING DIAGRAM*

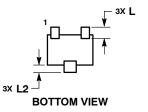


= Specific Device Code XX Μ = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G", may or not be present.

-X-2X b ⊕ 0.08 X Y **TOP VIEW**

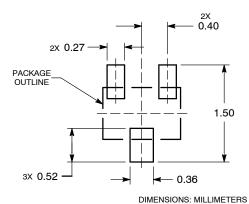




STYLE 1: PIN 1. BASE 2. EMITTER 3. COLLECTOR STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE

STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE STYLE 5: PIN 1. GATE 2. SOURCE 3. DRAIN

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	SOT-723		PAGE 1 OF 1

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